

INFORMATION DISCLOSURE
CITATION IN AN
APPLICATION

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APPLICANT
Hideto HIDAHA

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GROUP

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U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
LP	5,640,343	06/17/97	Gallagher, et al.			
LP	6,081,445	06/27/00	Shi, et al.			

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EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

LP	Scheuerlein, et al., "A 10ns Read and Write Non-Volatile Memory Array Using A Magnetic Tunnel Junction and FET Switch in Each Cell" ISSCC Digest of Technical Papers, TA7.2, February 2000, pages 94-95, 128-129, 409-410
	Durlam, et al, "Nonvolatile RAM Based On Magnetic Tunnel Junction Elements, ISSCC Digest of Technical Papers, TA7.3, February 2000, pages 96-97, 130-131, 410-411
LP	Numata, et al., "Magnetic Random Access Memory(MRAM), Technical Report of IEICE, March 2000, pages 13-18
	Naji, et al., "A 256kb 3.0V 1TMTJ Nonvolatile Magnetoresistive RAM" ISSCC Digest of Technical Papers, TA7.6, February 6, 2001, pages 94-95, 122-123, 404-405, 438
LP	US Patent Application Serial No. 09/887,321, Filed June 25, 2001, Atty. Docket No. 57454-137
LP	US Patent Application Serial No. 09/834,638, Filed April 16, 2001, Atty. Docket No. 57454-075
LP	US Patent Application Serial No. 09/805,043, Filed March 14, 2001, Atty. Docket No. 57454-039
LP	US Patent Application Serial No. 09/832,025, Filed April 11, 2001, Atty. Docket No. 57454-070
LP	US Patent Application Serial No. 09/852,087, Filed May 10, 2001, Atty. Docket No. 57454-111
LP	US Patent Application Serial No. 09/944, 346, Filed September 4, 2001, Atty. Docket. No. 57454-189

EXAMINER

DATE CONSIDERED

02/12/2003